



September 2017

ON Semiconductor®

# ISL9R3060G2, ISL9R3060P2

## 30 A, 600 V, STEALTH™ Diode

### Features

- Stealth Recovery  $t_{rr} = 36\text{ns}$  (@  $I_F = 30\text{ A}$ )
- Max Forward Voltage,  $V_F = 2.4\text{ V}$  (@  $T_C = 25^\circ\text{C}$ )
- 600 V Reverse Voltage and High Reliability
- Avalanche Energy Rated
- RoHS Compliant

### Applications

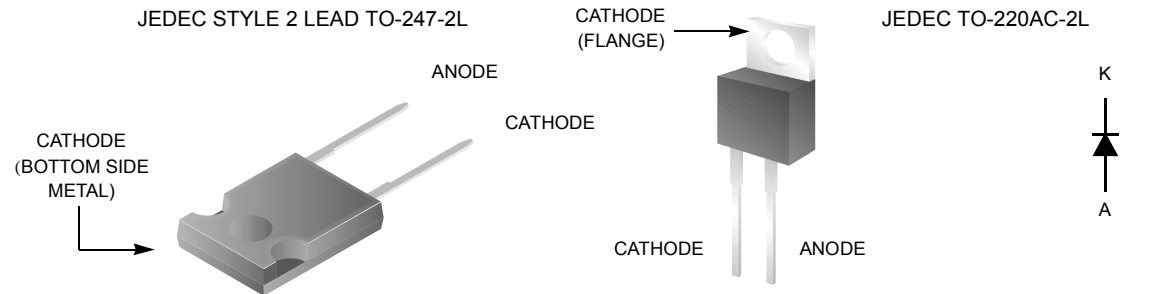
- SMPS
- Hard Switched PFC Boost Diode
- UPS Free Wheeling Diode
- Motor Drive FWD
- SMPS FWD
- Snubber Diode

### Description

The ISL9R3060G2, ISL9R3060P2 is a STEALTH™ diode optimized for low loss performance in high frequency hard switched applications. The STEALTH™ family exhibits low reverse recovery current ( $I_{rr}$ ) and exceptionally soft recovery under typical operating conditions. This device is intended for use as a free wheeling or boost diode in power supplies and other power switching applications. The low  $I_{rr}$  and short  $t_a$  phase reduce loss in switching transistors. The soft recovery minimizes ringing, expanding the range of conditions under which the diode may be operated without the use of additional snubber circuitry. Consider using the STEALTH™ diode with an SMPS IGBT to provide the most efficient and highest power density design at lower cost.

### Package

### Symbol



### Device Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Unit
$V_{RRM}$	Peak Repetitive Reverse Voltage	600	V
$V_{RWM}$	Working Peak Reverse Voltage	600	V
$V_R$	DC Blocking Voltage	600	V
$I_{F(AV)}$	Average Rectified Forward Current	30	A
$I_{FRM}$	Repetitive Peak Surge Current (20kHz Square Wave)	70	A
$I_{FSM}$	Nonrepetitive Peak Surge Current (Halfwave 1 Phase 60Hz)	325	A
$P_D$	Power Dissipation	200	W
$E_{AVL}$	Avalanche Energy (1A, 40mH)	20	mJ
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to 175	$^\circ\text{C}$
$T_L$	Maximum Temperature for Soldering	300	$^\circ\text{C}$
$T_{PKG}$	Leads at 0.063in (1.6mm) from Case for 10s Package Body for 10s, See Techbrief TB334	260	$^\circ\text{C}$

CAUTION: Stresses above those listed in "Device Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

ISL9R3060G2, ISL9R3060P2 — STEALTH™ Diode

### Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
ISL9R3060G2	R3060G2	TO-247-2L	Tube	N/A	N/A	30
ISL9R3060P2	R3060P2	TO-220AC-2L	Tube	N/A	N/A	50

### Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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#### Off State Characteristics

$I_R$	Instantaneous Reverse Current	$V_R = 600\text{ V}$	$T_C = 25^\circ\text{C}$	-	-	100	$\mu\text{A}$
			$T_C = 125^\circ\text{C}$	-	-	1.0	$\text{mA}$

#### On State Characteristics

$V_F$	Instantaneous Forward Voltage	$I_F = 30\text{ A}$	$T_C = 25^\circ\text{C}$	-	2.1	2.4	$\text{V}$
			$T_C = 125^\circ\text{C}$	-	1.7	2.1	$\text{V}$

#### Dynamic Characteristics

$C_J$	Junction Capacitance	$V_R = 10\text{ V}, I_F = 0\text{ A}$	-	120	-	$\text{pF}$
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#### Switching Characteristics

$t_{rr}$	Reverse Recovery Time	$I_F = 1\text{ A}, di_F/dt = 100\text{ A}/\mu\text{s}, V_R = 30\text{ V}$	-	27	35	$\text{ns}$
			$I_F = 30\text{ A}, di_F/dt = 100\text{ A}/\mu\text{s}, V_R = 30\text{ V}$	-	36	45
$t_{rr}$	Reverse Recovery Time	$I_F = 30\text{ A}, di_F/dt = 200\text{ A}/\mu\text{s}, V_R = 390\text{ V}, T_C = 25^\circ\text{C}$	-	36	-	$\text{ns}$
$I_{rr}$	Reverse Recovery Current		-	2.9	-	$\text{A}$
$Q_{rr}$	Reverse Recovery Charge		-	55	-	$\text{nC}$
$t_{rr}$	Reverse Recovery Time		-	110	-	$\text{ns}$
S	Softness Factor ( $t_b/t_a$ )		-	1.9	-	
$I_{rr}$	Reverse Recovery Current	$I_F = 30\text{ A}, di_F/dt = 200\text{ A}/\mu\text{s}, V_R = 390\text{ V}, T_C = 125^\circ\text{C}$	-	6	-	$\text{A}$
$Q_{rr}$	Reverse Recovery Charge		-	450	-	$\text{nC}$
$t_{rr}$	Reverse Recovery Time		-	60	-	$\text{ns}$
S	Softness Factor ( $t_b/t_a$ )		-	1.25	-	
$I_{rr}$	Reverse Recovery Current		-	21	-	$\text{A}$
$Q_{rr}$	Reverse Recovery Charge	$I_F = 30\text{ A}, di_F/dt = 1000\text{ A}/\mu\text{s}, V_R = 390\text{ V}, T_C = 125^\circ\text{C}$	-	730	-	$\text{nC}$
$di_M/dt$	Maximum $di/dt$ during $t_b$		-	800	-	$\text{A}/\mu\text{s}$

#### Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance Junction to Case		-	-	0.75	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	TO-247	-	-	30	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	TO-220	-	-	62	$^\circ\text{C}/\text{W}$

Typical Performance Curves

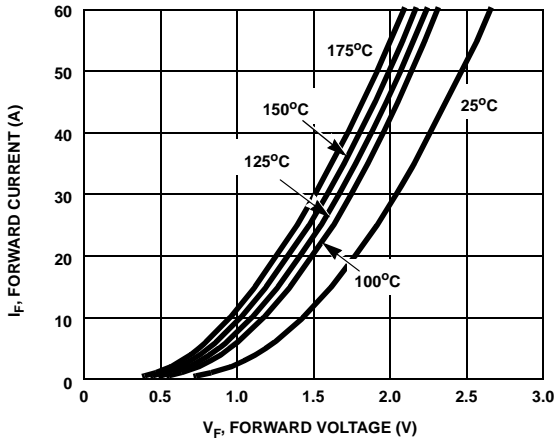


Figure 1. Forward Current vs Forward Voltage

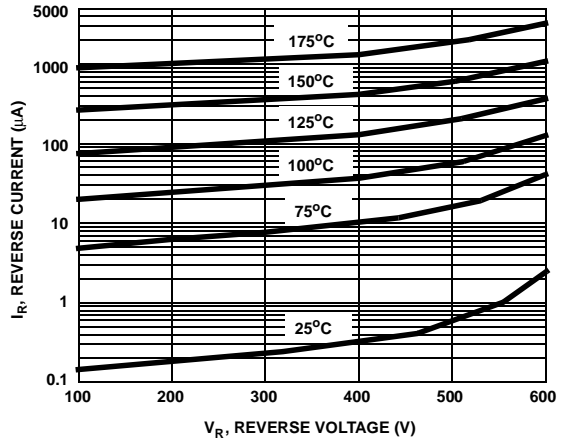


Figure 2. Reverse Current vs Reverse Voltage

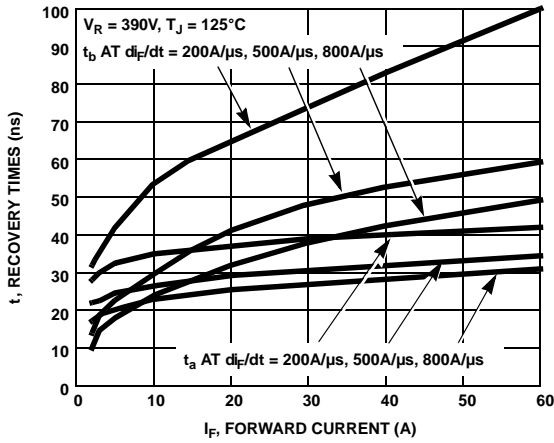


Figure 3.  $t_a$  and  $t_b$  Curves vs Forward Current

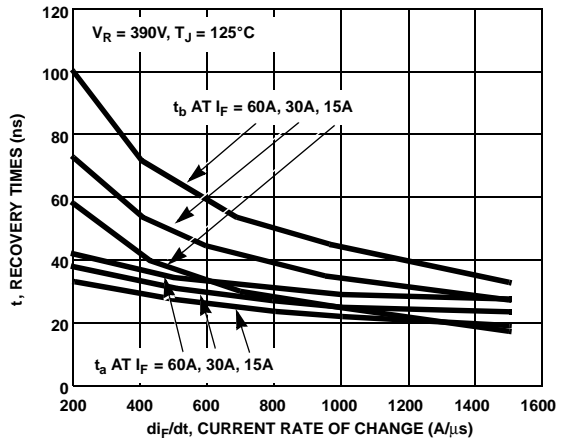


Figure 4.  $t_a$  and  $t_b$  Curves vs  $di_F/dt$

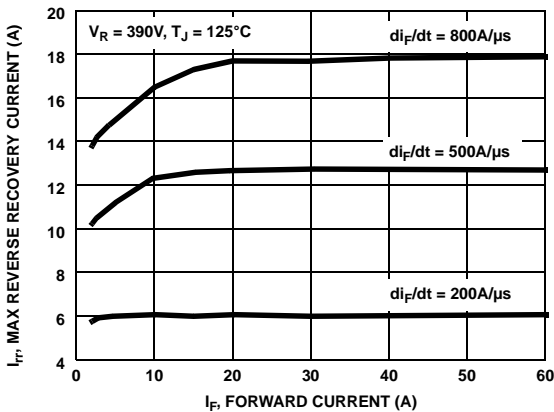


Figure 5. Maximum Reverse Recovery Current vs Forward Current

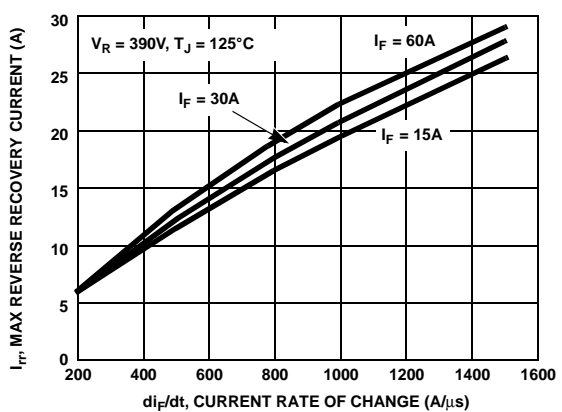


Figure 6. Maximum Reverse Recovery Current vs  $di_F/dt$

Typical Performance Curves (Continued)

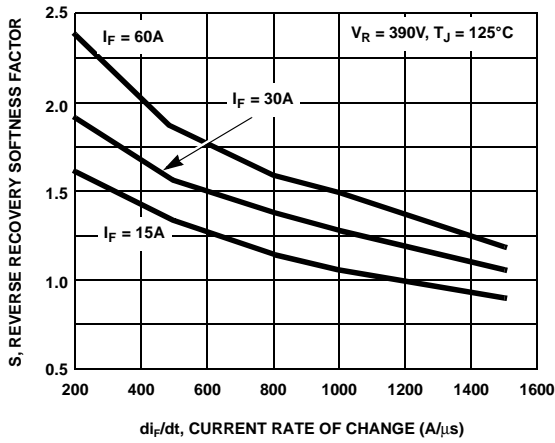


Figure 7. Reverse Recovery Softness Factor vs  $di_F/dt$

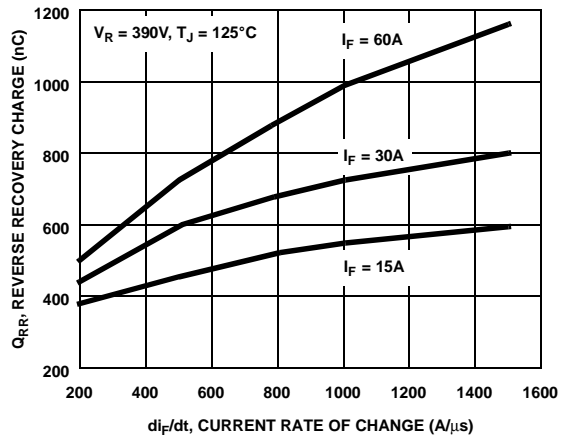


Figure 8. Reverse Recovery Charge vs  $di_F/dt$

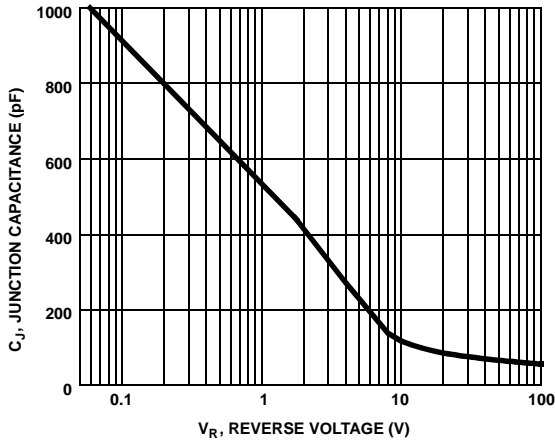


Figure 9. Junction Capacitance vs Reverse Voltage

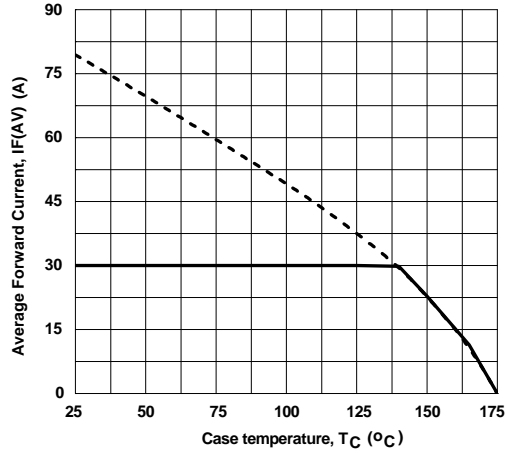


Figure 10. Forward Current Derating Curve

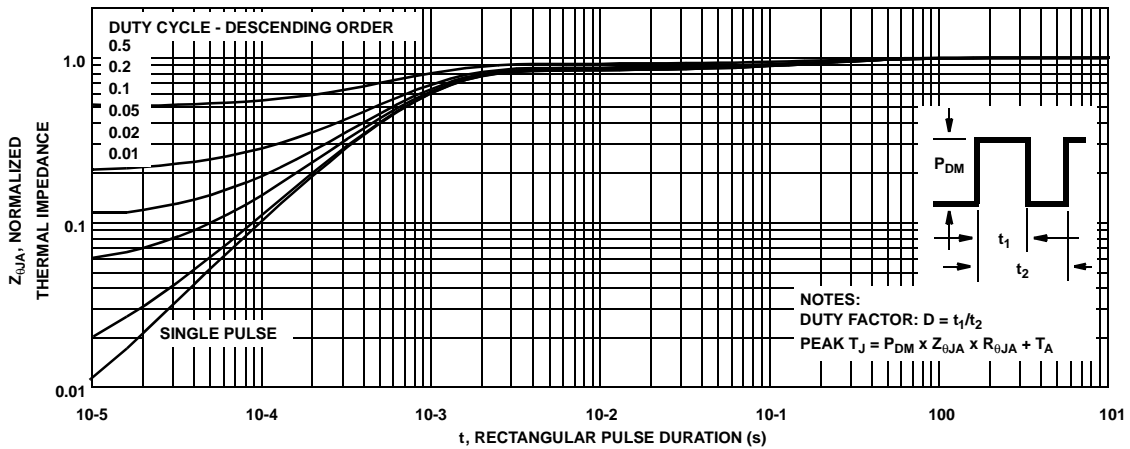


Figure 11. Normalized Maximum Transient Thermal Impedance

## Test Circuit and Waveforms

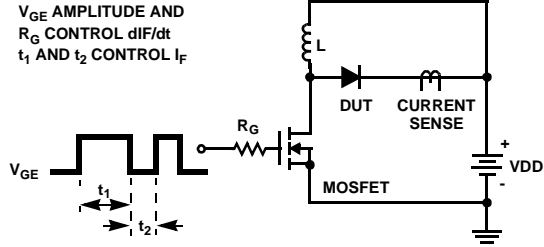


Figure 12.  $t_{rr}$  Test Circuit

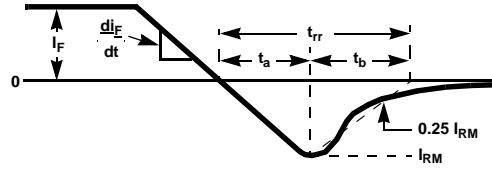


Figure 13.  $t_{rr}$  Waveforms and Definitions

$I = 1A$   
 $L = 40mH$   
 $R < 0.1\Omega$   
 $V_{DD} = 50V$   
 $E_{AVL} = 1/2LI^2 [V_{R(AVL)}/(V_{R(AVL)} - V_{DD})]$   
 $Q1 = IGBT (BV_{CES} > DUT V_{R(AVL)})$

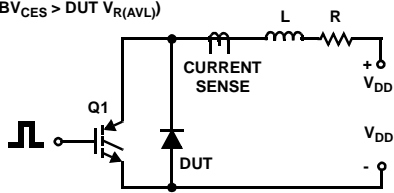


Figure 14. Avalanche Energy Test Circuit

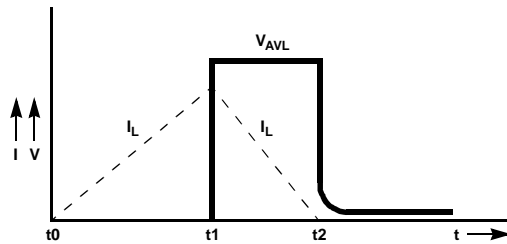
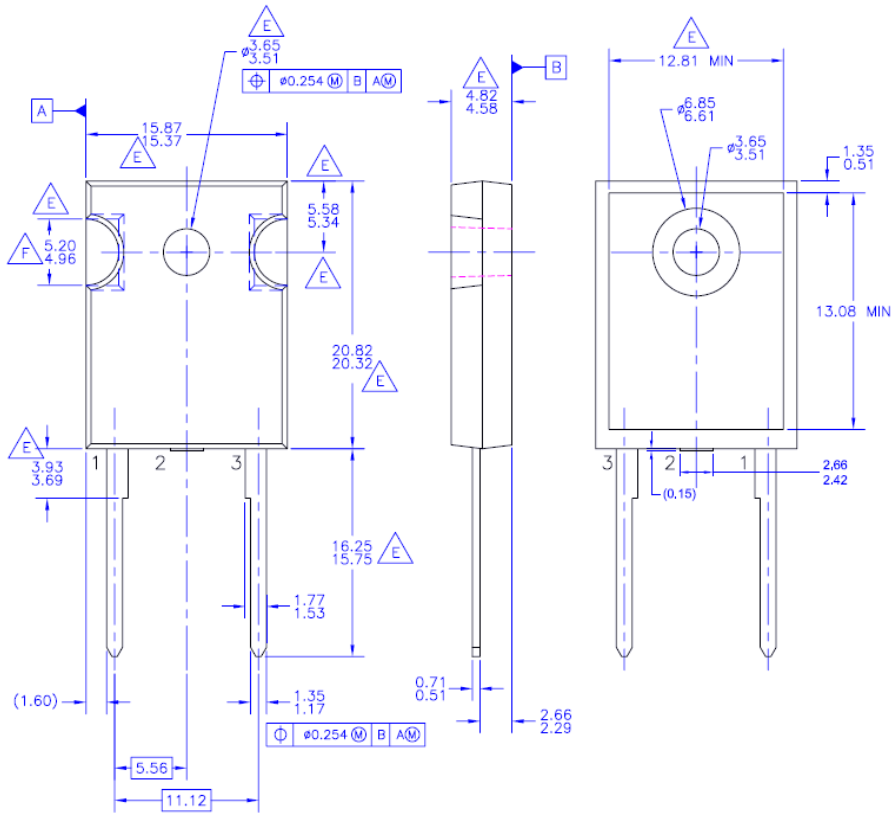


Figure 15. Avalanche Current and Voltage Waveforms

**Mechanical Dimensions**



- NOTES: UNLESS OTHERWISE SPECIFIED  
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 B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.  
 C. ALL DIMENSIONS ARE IN MILLIMETERS.  
 D. DRAWING CONFORMS TO ASME Y14.5 - 1994  
 E. DOES NOT COMPLY JEDEC STANDARD VALUE  
 F. NOTCH MAY BE SQUARE  
 G. DRAWING FILENAME: MKT-TO247B02\_REV02

**Figure 16. TO-247 2L - TO247,MOLDED,2LD, JEDEC OPTION AB**

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